

# Aminul Islam

## List of Publications by Citations

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161  
papers

1,057  
citations

16  
h-index

26  
g-index

197  
ext. papers

1,511  
ext. citations

1.5  
avg, IF

5.39  
L-index

#	Paper	IF	Citations
161	. <i>IEEE Transactions on Electron Devices</i> , <b>2012</b> , 59, 631-638	2.9	90
160	Variation Tolerant Differential 8T SRAM Cell for Ultralow Power Applications. <i>IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems</i> , <b>2016</b> , 35, 549-558	2.5	67
159	A technique to mitigate impact of process, voltage and temperature variations on design metrics of SRAM Cell. <i>Microelectronics Reliability</i> , <b>2012</b> , 52, 405-411	1.2	61
158	. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2016</b> , 16, 172-182	1.6	51
157	Optimized Design of a 32-nm CNFET-Based Low-Power Ultrawideband CCII. <i>IEEE Nanotechnology Magazine</i> , <b>2012</b> , 11, 1100-1109	2.6	33
156	Effect of potassium fertilization on yield and potassium nutrition of Boro rice in a wetland ecosystem of Bangladesh. <i>Archives of Agronomy and Soil Science</i> , <b>2016</b> , 62, 1530-1540	2	30
155	Advances in Ultrasonic Welding of Thermoplastic Composites: A Review. <i>Materials</i> , <b>2020</b> , 13,	3.5	26
154	Variability aware low leakage reliable SRAM cell design technique. <i>Microelectronics Reliability</i> , <b>2012</b> , 52, 1247-1252	1.2	25
153	Floating active inductor based Class-C VCO with 8 digitally tuned sub-bands. <i>AEU - International Journal of Electronics and Communications</i> , <b>2018</b> , 83, 1-10	2.8	24
152	Characterization of Half-Select Free Write Assist 9T SRAM Cell. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 4745-4752	2.9	24
151	A 2.5 GHz Low Power, High- $Q$ , Reliable Design of Active Bandpass Filter. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2017</b> , 17, 229-244	1.6	22
150	A highly stable reliable SRAM cell design for low power applications. <i>Microelectronics Reliability</i> , <b>2020</b> , 105, 113503	1.2	21
149	Half-Select-Free Low-Power Dynamic Loop-Cutting Write Assist SRAM Cell for Space Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 80-89	2.9	21
148	Circuit-level design technique to mitigate impact of process, voltage and temperature variations in complementary metal-oxide semiconductor full adder cells. <i>IET Circuits, Devices and Systems</i> , <b>2015</b> , 9, 204-212	1.1	20
147	Transmission gate-based 9T SRAM cell for variation resilient low power and reliable internet of things applications. <i>IET Circuits, Devices and Systems</i> , <b>2019</b> , 13, 584-595	1.1	18
146	Variation resilient subthreshold SRAM cell design technique. <i>International Journal of Electronics</i> , <b>2012</b> , 99, 1223-1237	1.2	18
145	Optimization of SiC UMOSFET Structure for Improvement of Breakdown Voltage and ON-Resistance. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 615-621	2.9	16

144	Design of Power- and Variability-Aware Nonvolatile RRAM Cell Using Memristor as a Memory Element. <i>IEEE Journal of the Electron Devices Society</i> , <b>2019</b> , 7, 701-709	2.3	16
143	Characterization of AlGaIn/GaN and AlGaIn/AlN/GaN HEMTs in terms of mobility and subthreshold slope. <i>Journal of Computational Electronics</i> , <b>2016</b> , 15, 172-180	1.8	15
142	Reliable and $\$Q\$$ -Enhanced Floating Active Inductors and Their Application in RF Bandpass Filters. <i>IEEE Access</i> , <b>2018</b> , 6, 48181-48194	3.5	13
141	Quality investigation of miniaturized Moulded Interconnect Devices (MIDs) for hearing aid applications. <i>CIRP Annals - Manufacturing Technology</i> , <b>2015</b> , 64, 539-544	4.9	12
140	Effect of Process Parameters on Flow Length and Flash Formation in Injection Moulding of High Aspect Ratio Polymeric Micro Features. <i>Micromachines</i> , <b>2018</b> , 9,	3.3	12
139	Reliable write assist low power SRAM cell for wireless sensor network applications. <i>IET Circuits, Devices and Systems</i> , <b>2020</b> , 14, 137-147	1.1	11
138	Variability analysis and FinFET-based design of XOR and XNOR circuit <b>2011</b> ,		11
137	VARIABILITY ANALYSIS OF 6T AND 7T SRAM CELL IN SUB-45NM TECHNOLOGY. <i>IJUM Engineering Journal</i> , <b>2011</b> , 12, 13-30	1.2	11
136	Direct electroplating of plastic for advanced electrical applications. <i>CIRP Annals - Manufacturing Technology</i> , <b>2017</b> , 66, 209-212	4.9	10
135	Variation-aware widely tunable nanoscale design of CMOS active inductor-based RF bandpass filter. <i>International Journal of Circuit Theory and Applications</i> , <b>2017</b> , 45, 2181-2200	2	9
134	Nonvolatile and Robust Design of Content Addressable Memory Cell Using Magnetic Tunnel Junction at Nanoscale Regime. <i>IEEE Transactions on Magnetics</i> , <b>2015</b> , 51, 1-13	2	9
133	Design and development of memristor-based RRAM. <i>IET Circuits, Devices and Systems</i> , <b>2019</b> , 13, 548-557	1.1	9
132	TG based 2T2M RRAM using Memristor as Memory Element. <i>Indian Journal of Science and Technology</i> , <b>2016</b> , 9,	1	9
131	Design of 10T full adder cell for ultralow-power applications. <i>Ain Shams Engineering Journal</i> , <b>2018</b> , 9, 2363-2372	4.4	8
130	Comparative study of CMOS- and FinFET-based 10T SRAM cell in subthreshold regime <b>2014</b> ,		8
129	Implementation of FinFET based STT-MRAM bitcell <b>2014</b> ,		8
128	A CMOS active inductor based digital and analog dual tuned voltage-controlled oscillator. <i>Microsystem Technologies</i> , <b>2019</b> , 25, 1571-1583	1.7	8
127	Design of differential TG based 8T SRAM cell for ultralow-power applications. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 3299-3310	1.7	8

126	Correlation of mechanical and electrical properties with processing variables in MWCNT reinforced thermoplastic nanocomposites. <i>Journal of Composite Materials</i> , <b>2018</b> , 52, 3681-3697	2.7	7
125	Gate Design in Injection Molding of Microfluidic Components Using Process Simulations. <i>Journal of Micro and Nano-Manufacturing</i> , <b>2016</b> , 4,	1.3	7
124	Trigger Pulse Generator Using Proposed Buffered Delay Model and Its Application. <i>Active and Passive Electronic Components</i> , <b>2015</b> , 2015, 1-9	0.3	7
123	Robust Design of CNFET Based Buffered Delay Model and Microwave Pulse Generator <b>2014</b> ,		7
122	Study of high Al fraction in AlGa <sub>N</sub> barrier HEMT and GaN and InGa <sub>N</sub> channel HEMT with In <sub>0.17</sub> Al <sub>0.83</sub> N barrier. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 2145-2158	1.7	7
121	Characterization of InP-based pseudomorphic HEMT with T-gate. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 2183-2191	1.7	7
120	Design of memristor based low power and highly reliable ReRAM cell. <i>Microsystem Technologies</i> , <b>2019</b> , 1	1.7	6
119	Soft-Error Resilient Read Decoupled SRAM With Multi-Node Upset Recovery for Space Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 68, 2246-2254	2.9	6
118	Design of Soft-Error-Aware SRAM With Multi-Node Upset Recovery for Aerospace Applications. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , <b>2021</b> , 68, 2470-2480	3.9	6
117	Analytical Modeling of Wrap-Gate Carbon Nanotube FET With Parasitic Capacitances and Density of States. <i>IEEE Transactions on Electron Devices</i> , <b>2016</b> , 63, 3314-3319	2.9	6
116	Comprehensive characterization and material modeling for ceramic injection molding simulation performance validations. <i>International Journal of Advanced Manufacturing Technology</i> , <b>2019</b> , 102, 225-240 <sup>2</sup>	3.2	6
115	Interaction of nanofillers in injection-molded graphene/carbon nanotube reinforced PA66 hybrid nanocomposites. <i>Journal of Polymer Engineering</i> , <b>2018</b> , 38, 971-981	1.4	6
114	Technology scaling and its side effects <b>2015</b> ,		5
113	Experimental investigation of new manufacturing process chains to create micro-metal structures on polymer substrates for lab-on-chip sensors. <i>International Journal of Advanced Manufacturing Technology</i> , <b>2012</b> , 59, 101-109	3.2	5
112	Characterization of AlGa <sub>N</sub> and GaN Based HEMT with AlN Interfacial Spacer <b>2015</b> ,		5
111	Power - and variability-aware design of FinFET-based XOR circuit at nanoscale regime <b>2014</b> ,		5
110	Robust subthreshold full adder design technique <b>2011</b> ,		5
109	A VDTA-based robust electronically tunable memristor emulator circuit. <i>Analog Integrated Circuits and Signal Processing</i> , <b>2020</b> , 104, 47-59	1.2	5

108	The Influence of the Hybridization Process on the Mechanical and Thermal Properties of Polyoxymethylene (POM) Composites with the Use of a Novel Sustainable Reinforcing System Based on Biocarbon and Basalt Fiber (BC/BF). <i>Materials</i> , <b>2020</b> , 13,	3.5	5
107	Design of CNFET based power- and variability-aware nonvolatile RRAM cell. <i>Microelectronics Journal</i> , <b>2019</b> , 86, 7-14	1.8	5
106	Variation resilient low-power memristor-based synchronous flip-flops: design and analysis. <i>Microsystem Technologies</i> , <b>2021</b> , 27, 525-538	1.7	5
105	Highly Stable Low Power Radiation Hardened Memory-by-Design SRAM for Space Applications. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , <b>2021</b> , 68, 2147-2151	3.5	5
104	Design of a Stable Read-Decoupled 6T SRAM Cell at 16-Nm Technology Node <b>2015</b> ,		4
103	A Compact Low Power High Frequency Pulse Generator <b>2015</b> ,		4
102	Design of SRAM cell for low power portable healthcare applications. <i>Microsystem Technologies</i> , <b>2020</b> , 1	1.7	4
101	Architecture of resistive RAM with write driver. <i>Solid State Electronics Letters</i> , <b>2020</b> , 2, 10-22	0.6	4
100	Circuit-Level Technique to Design Variation- and Noise-Aware Reliable Dynamic Logic Gates. <i>IEEE Transactions on Device and Materials Reliability</i> , <b>2018</b> , 18, 224-239	1.6	4
99	Comparative analysis of D flip-flops in terms of delay and its variability <b>2015</b> ,		4
98	Notice of Removal: Optimized design of Au-polysilicon electrothermal microgripper for handling micro objects <b>2015</b> ,		4
97	Variability Analysis of MTJ-Based Circuit <b>2012</b> ,		4
96	Design of resistive random access memory cell and its architecture. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 1325-1332	1.7	4
95	Design and analysis of MISO bi-quad active filter. <i>International Journal of Electronics</i> , <b>2019</b> , 106, 287-304 <sup>1.2</sup>		4
94	Power-aware source feedback single-ended 7T SRAM cell at nanoscale regime. <i>Microsystem Technologies</i> , <b>2019</b> , 25, 1783-1791	1.7	4
93	Comparative analysis of AlGaIn/GaN high electron mobility transistor with sapphire and 4H-SiC substrate. <i>Microsystem Technologies</i> , <b>2019</b> , 25, 1927-1935	1.7	4
92	Low-power half-select free single-ended 10 transistor SRAM cell. <i>Microsystem Technologies</i> , <b>2017</b> , 23, 4133-4144	1.7	3
91	Current-mode circuit-level technique to design variation-aware nanoscale summing circuit for ultra-low power applications. <i>Microsystem Technologies</i> , <b>2017</b> , 23, 4045-4056	1.7	3

90	CNFET Based Voltage Multiplier Circuit for RF Energy Harvesting Applications <b>2015</b> ,		3
89	Device bias technique to improve design metrics of 6T SRAM cell for subthreshold operation <b>2015</b> ,		3
88	Analysis of various delay elements @ 16-nm technology node <b>2017</b> ,		3
87	Design of magnetic tunnel junction-based tunable spin torque oscillator at nanoscale regime. <i>IET Circuits, Devices and Systems</i> , <b>2016</b> , 10, 121-129	1.1	3
86	Design of variation-resilient CNFET-based Schmitt trigger circuits with optimum hysteresis at 16-nm technology node <b>2013</b> ,		3
85	Analysis of AlGaIn/GaN high electron mobility transistor for high frequency application <b>2017</b> ,		3
84	Revisiting performance of various delay elements to realize a trigger pulse generator <b>2015</b> ,		3
83	Design and Analysis of Robust Dual Threshold CMOS Full Adder Circuit in 32nm Technology <b>2010</b> ,		3
82	Variability Immune FinFET-Based Full Adder Design in Subthreshold Region <b>2011</b> ,		3
81	A Monotonic Digitally Controlled Delay Element-Based Programmable Trigger Pulse Generator. <i>Advances in Intelligent Systems and Computing</i> , <b>2016</b> , 365-374	0.4	3
80	Design of low power, variation tolerant single bitline 9T SRAM cell in 16-nm technology in subthreshold region. <i>Microelectronics Reliability</i> , <b>2021</b> , 120, 114126	1.2	3
79	Low Power and High Variation Tolerant 9T-SRAM Cell at 16-nm Technology Node. <i>Indian Journal of Science and Technology</i> , <b>2016</b> , 9,	1	3
78	Soft-Error-Aware Read-Decoupled SRAM With Multi-Node Recovery for Aerospace Applications. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , <b>2021</b> , 68, 3336-3340	3.5	3
77	Threshold voltage extraction and its reliance on device parameters @ 16-nm process technology <b>2015</b> ,		2
76	Design of hybrid full adder in deep subthreshold region for ultralow power applications <b>2015</b> ,		2
75	Which is the Best 2-to-1 Line Multiplexer for Ultralow-Power Applications? <b>2015</b> ,		2
74	Comparative study of subthreshold leakage in CNFET & MOSFET @ 32-nm technology node <b>2016</b> ,		2
73	A comparative analysis of various programmable delay elements using predictive technology model <b>2016</b> ,		2

72	Multi-gate device and summing-circuit co-design robustness studies @ 32-nm technology node. <i>Microsystem Technologies</i> , <b>2017</b> , 23, 4099-4109	1.7	2
71	Analysis of breakdown voltage of a field plated High Electron Mobility Transistor <b>2017</b> ,		2
70	CNFET-Based 0.1- to 1.2-V DC/DC Boost Converter With Voltage Regulation for Energy Harvesting Applications. <i>IEEE Nanotechnology Magazine</i> , <b>2015</b> , 14, 660-667	2.6	2
69	CNFET-based ternary inverter and its variability analysis <b>2014</b> ,		2
68	Performance evaluation of MCML-based XOR/XNOR circuit at 16-nm Technology node <b>2014</b> ,		2
67	CNFET-based 0.1 V to 0.6 V DC/DC converter <b>2014</b> ,		2
66	FinFET-based variation resilient 8T SRAM cell <b>2012</b> ,		2
65	Design and Analysis of Robust Spin Transfer Torque Magnetic Random Access Memory Bitcell Using FinFET. <i>Journal of Low Power Electronics</i> , <b>2014</b> , 10, 220-227	1.2	2
64	Characterization of single-ended 9T SRAM cell. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 1591-1604	1.7	2
63	An Analysis and Modeling of the Class-E Inverter for ZVS/ZVDS at Any Duty Ratio with High Input Ripple Current. <i>Electronics (Switzerland)</i> , <b>2021</b> , 10, 1312	2.6	2
62	Experimental Investigation of Comparative Process Capabilities of Metal and Ceramic Injection Molding for Precision Applications. <i>Journal of Micro and Nano-Manufacturing</i> , <b>2016</b> , 4,	1.3	2
61	Characterisation of field plated high electron mobility transistor <b>2016</b> ,		2
60	Study of variability performance of CMOS active inductors. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 3101-3111	1.7	2
59	A novel CNFET based tunable memristor emulator. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 2173-2181	1.7	2
58	Radiation-hardened read-decoupled low-power 12T SRAM for space applications. <i>International Journal of Circuit Theory and Applications</i> ,	2	2
57	Soft-Error-Immune Read-Stability-Improved SRAM for Multi-Node Upset Tolerance in Space Applications. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , <b>2021</b> , 68, 3317-3327	3.9	2
56	A Comparative Performance Analysis of Zero Voltage Switching Class E and Selected Enhanced Class E Inverters. <i>Electronics (Switzerland)</i> , <b>2021</b> , 10, 2226	2.6	2
55	Comparative analysis of various 9T SRAM cell at 22-nm technology node <b>2015</b> ,		1

54	High breakdown (958 V) low threshold GaN HEMT <b>2017</b> ,		1
53	Performance comparison of AlGaN/GaN HFET with sapphire and 4H-SiC substrate <b>2017</b> ,		1
52	Development of HEMT device with surface passivation for a low leakage current and steep subthreshold slope <b>2017</b> ,		1
51	Compact Versatile Noise Suppressed Programmable Trigger Pulse Generator for Industrial Applications. <i>The National Academy of Sciences, India</i> , <b>2018</b> , 41, 97-101	0.6	1
50	Performance Enhancement of Full Adder Circuit: Current Mode Operated Majority Function Based Design. <i>Advances in Intelligent Systems and Computing</i> , <b>2018</b> , 569-578	0.4	1
49	Robustness study and CNFET realization of optimal logic circuit for ultralow power applications <b>2014</b> ,		1
48	Design of 2:1 multiplexer and 1:2 demultiplexer using magnetic tunnel junction elements <b>2013</b> ,		1
47	Analysis of Al <sub>0.22</sub> Ga <sub>0.78</sub> As/In <sub>0.18</sub> Ga <sub>0.82</sub> As/GaAs Pseudomorphic HEMT device with higher conductivity <b>2017</b> ,		1
46	Low-power 9T subthreshold SRAM cell with single-ended write scheme <b>2015</b> ,		1
45	7-Transistor 2-memristor based non-volatile static random access memory cell design <b>2015</b> ,		1
44	MOSFET aspect ratio optimization for minimized transistor mismatch at UDSM technology nodes <b>2015</b> ,		1
43	Highly stable subthreshold single-ended 7T SRAM cell <b>2014</b> ,		1
42	Power and variability analysis of CMOS logic families @ 22-nm technology node <b>2014</b> ,		1
41	Stability and variability enhancement of 9T SRAM cell for subthreshold operation <b>2014</b> ,		1
40	Performance evaluation of CNFET based operational amplifier at technology node beyond 45-nm <b>2013</b> ,		1
39	Power optimized variation aware dual-threshold SRAM cell design technique. <i>Nanotechnology, Science and Applications</i> , <b>2011</b> , 4, 25-33	3.9	1
38	Effect of Source, Drain and Channel Spacing from Gate of HEMT. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 81-90	0.2	1
37	Indium Phosphide Based Dual Gate High Electron Mobility Transistor. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 255-264	0.2	1



36	Study and Analysis of AlInN/GaN Based High Electron Mobility Transistor. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 449-459	0.2	1
35	A VDIBA Based Voltage-Mode Highpass and Bandpass Filter. <i>Communications in Computer and Information Science</i> , <b>2018</b> , 83-89	0.3	1
34	Process and Voltage Variation-Aware Design and Analysis of Active Grounded Inductor-Based Bandpass Filter. <i>Advances in Intelligent Systems and Computing</i> , <b>2018</b> , 309-315	0.4	1
33	A low power SRAM cell design for wireless sensor network applications. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 2325-2335	1.7	1
32	Low Voltage Charge Pump for RF Energy Harvesting Applications. <i>Indian Journal of Science and Technology</i> , <b>2016</b> , 9,	1	1
31	Validation of precision powder injection molding process simulations using a spiral test geometry <b>2016</b> ,		1
30	Investigation on electrical characteristics of FDSOI device for ultra-low power operation <b>2016</b> ,		1
29	An efficient circuit-level power reduction technique for ultralow power applications. <i>Microsystem Technologies</i> , <b>2019</b> , 25, 1689-1697	1.7	1
28	A low power, temperature compensated, robust design of CS amplifier in nanoscale regime. <i>Microsystem Technologies</i> , <b>2019</b> , 25, 1841-1852	1.7	1
27	Compact design of an MTJ-based non-volatile CAM cell with read/write operations. <i>Microsystem Technologies</i> , <b>2020</b> , 26, 3259-3270	1.7	1
26	A Highly Reliable and Radiation-Hardened Majority PFET-Based 10T SRAM Cell. <i>Lecture Notes in Electrical Engineering</i> , <b>2021</b> , 113-122	0.2	1
25	Al <sub>0.30</sub> Ga <sub>0.70</sub> N /GaN MODFET with triple-teeth metal for RF and high-power applications. <i>Physica Scripta</i> , <b>2022</b> , 97, 034003	2.6	0
24	Variation resilient reliable design of trigger pulse generator. <i>IET Circuits, Devices and Systems</i> , <b>2020</b> , 14, 860-868	1.1	0
23	High Speed Cache Design Using Multi-diameter CNFET at 32nm Technology. <i>Communications in Computer and Information Science</i> , <b>2010</b> , 215-222	0.3	0
22	Enhanced Energy Savings in Indoor Environments with Effective Daylight Utilization and Area Segregation. <i>Symmetry</i> , <b>2020</b> , 12, 1313	2.7	0
21	Characterization of AlGaN/GaN based HEMT for low noise and high frequency application. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , e2932	1	0
20	Process chains for the mass production of transparent crowns for posterior teeth. <i>CIRP Annals - Manufacturing Technology</i> , <b>2019</b> , 68, 591-594	4.9	
19	Multi-functional Active Filter Design Using Three VDTAs. <i>Communications in Computer and Information Science</i> , <b>2018</b> , 124-130	0.3	

18	Modeling and sizing of non-linear CMOS analog circuits used in mixed signal systems. <i>Analog Integrated Circuits and Signal Processing</i> , <b>2019</b> , 99, 95-109	1.2
17	Comparative Study of Active Inductor-Based Low-Noise Amplifiers. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 411-418	0.2
16	A Technique to Design Robust Single-Stage Operational Amplifier. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 469-478	0.2
15	A Current-Mode Memristor Emulator Circuit. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 493-501	0.2
14	Design of Fractional-Order Low-Pass and High-Pass Filter. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 535-542	0.2
13	Active Multifunctional Filter Design Using Carbon Nanotube Transistors. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 103-111	0.2
12	A Fully Integrated Tunable Memristor Emulator Circuit. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 553-560	0.6
11	Design of Robust Ratioed CMOS SR Latch. <i>Lecture Notes in Electrical Engineering</i> , <b>2020</b> , 429-441	0.2
10	Design of a Signal Sensor for Analyzing Biological Activities at Cellular Level. <i>Advances in Intelligent Systems and Computing</i> , <b>2015</b> , 405-412	0.4
9	Low-Leakage, Low-Power, High-Stable SRAM Cell Design. <i>Advances in Intelligent Systems and Computing</i> , <b>2016</b> , 549-556	0.4
8	Design of a Low-Delay-Write Model of a TMCAM. <i>Advances in Intelligent Systems and Computing</i> , <b>2016</b> , 41-47	0.4
7	Study and Analysis of Subthreshold Leakage Current in Sub-65 nm NMOSFET. <i>Advances in Intelligent Systems and Computing</i> , <b>2016</b> , 1-10	0.4
6	Estimation of MOS Capacitance Across Different Technology Nodes. <i>Advances in Intelligent Systems and Computing</i> , <b>2017</b> , 297-306	0.4
5	Cross-Coupled Dynamic CMOS Latches: Scalability Analysis. <i>Advances in Intelligent Systems and Computing</i> , <b>2017</b> , 307-315	0.4
4	Cross-Coupled Dynamic CMOS Latches: Robustness Study of Timing. <i>Advances in Intelligent Systems and Computing</i> , <b>2017</b> , 317-325	0.4
3	Investigating Phase Transform Behavior in Indium Selenide Based RAM and Its Validation as a Memory Element. <i>Journal of Materials</i> , <b>2016</b> , 2016, 1-7	0.7
2	An Electronically-Tuneable VDTA Based Sinusoidal Oscillator. <i>Communications in Computer and Information Science</i> , <b>2018</b> , 115-123	0.3
1	Optimization of InP HEMT Using Multilayered Cap and Asymmetric Gate Recess. <i>Communications in Computer and Information Science</i> , <b>2018</b> , 19-28	0.3

